



SANYO Semiconductors

DATA SHEET

EFC4612R — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- 2.5V drive.
- Built-in gate protection resistor.
- Best suited for LiB charging and discharging switch.
- Common-drain type.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	V _{SS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Source Current (DC)	I _S		6	A
Source Current (Pulse)	I _{SP}	PW≤10μs, duty cycle≤1%	60	A
Total Dissipation	P _T	When mounted on ceramic substrate (5000mm ² ×0.8mm)	1.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Source-to-Source Breakdown Voltage	V(BR)SSS	I _S =1mA, V _{GS} =0V	24			V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{SS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{SS} =10V, I _S =1mA	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _{SS} =10V, I _S =3A		3.1		S

Marking : FN

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EFC4612R

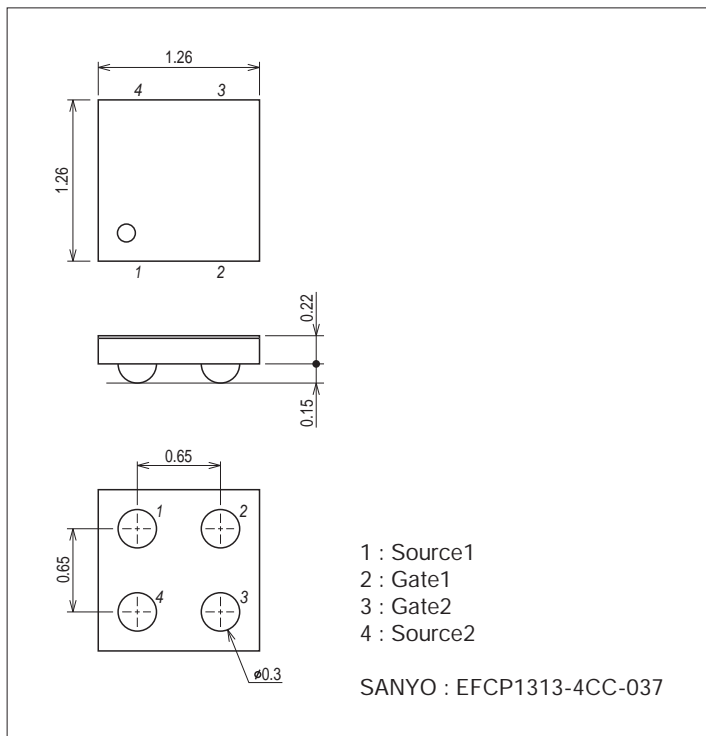
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Source-to-Source On-State Resistance	R _{SS(on)1}	I _S =3A, V _{GS} =4.5V Test Circuit 5	24	39	45	mΩ
	R _{SS(on)2}	I _S =3A, V _{GS} =4.0V Test Circuit 5	25	41	48	mΩ
	R _{SS(on)3}	I _S =3A, V _{GS} =3.7V Test Circuit 5	27.5	43	50	mΩ
	R _{SS(on)4}	I _S =3A, V _{GS} =3.1V Test Circuit 5	31.5	48	57	mΩ
	R _{SS(on)5}	I _S =3A, V _{GS} =2.5V Test Circuit 5	33.5	58	72	mΩ
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit. Test Circuit 7		20		ns
Rise Time	t _r	See specified Test Circuit. Test Circuit 7		230		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit. Test Circuit 7		130		ns
Fall Time	t _f	See specified Test Circuit. Test Circuit 7		210		ns
Total Gate Charge	Q _g	V _{SS} =10V, V _{GS} =4.5V, I _S =6A		7		nC
Forward Source-to-Source Voltage	V _{F(S-S)}	I _S =3A, V _{GS} =0V Test Circuit 6		0.8	1.2	V

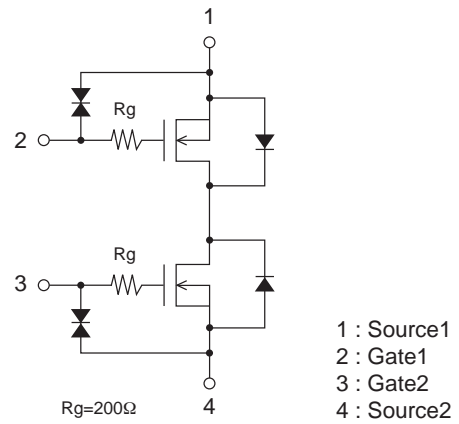
Package Dimensions

unit : mm (typ)

7064-001



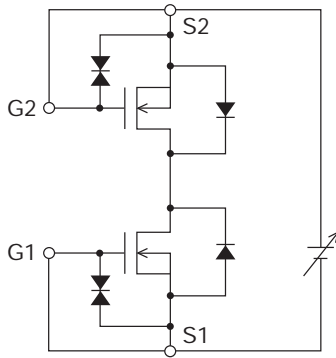
Electrical Connection



Test circuits are example of measuring FET1 side

Test Circuit 1

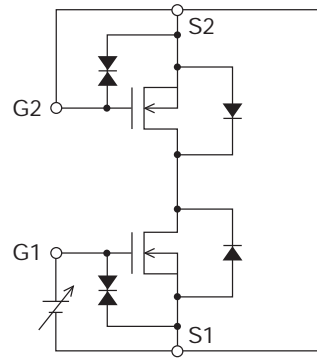
V_{SSS} / I_{SSS}



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Test Circuit 2

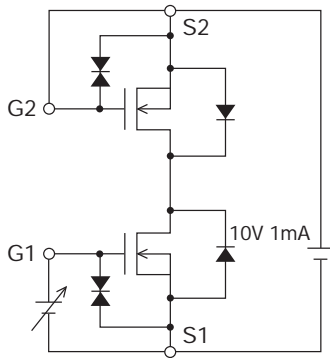
$I_{GSS(+)} / (-)$



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Test Circuit 3

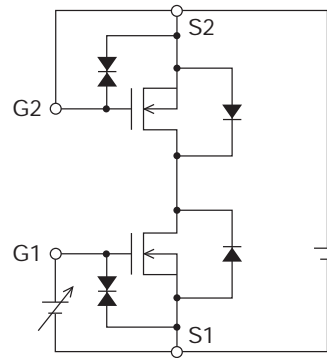
$V_{GS(off)}$



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Test Circuit 4

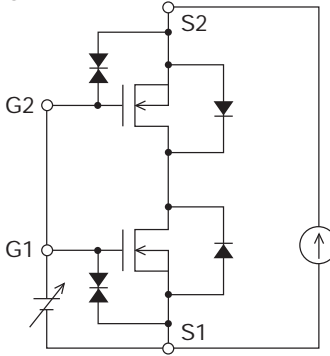
$|y_{fs}|$



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Test Circuit 5

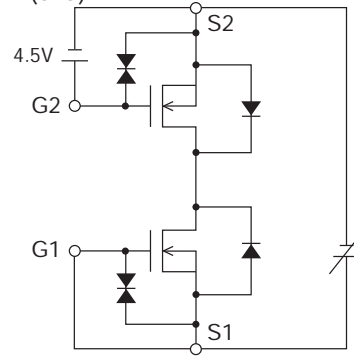
$R_{SS(on)}$



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Test Circuit 6

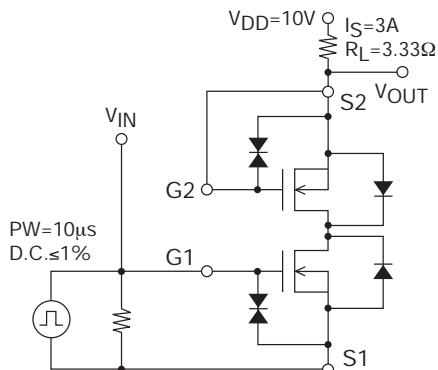
$V_{F(S-S)}$



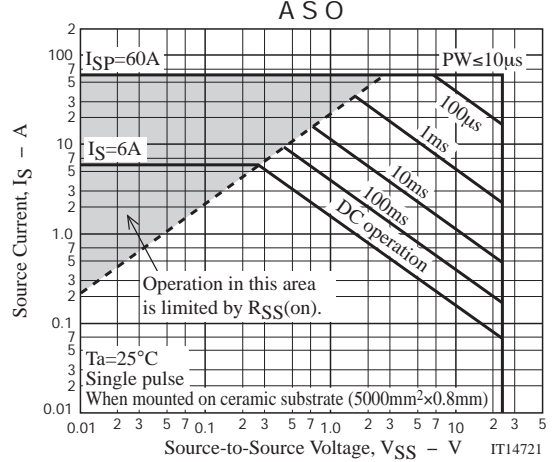
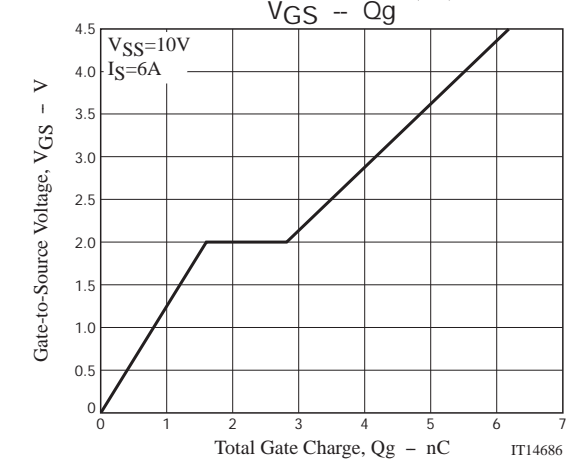
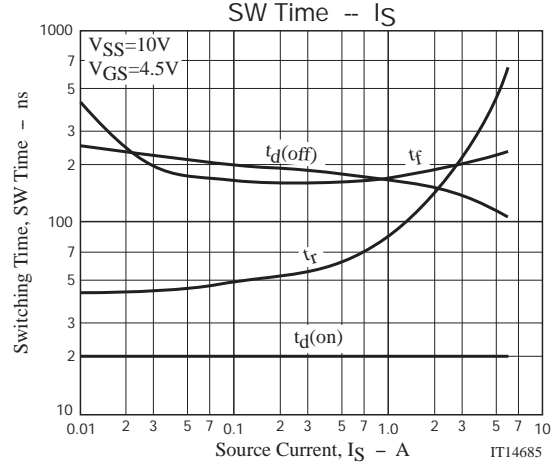
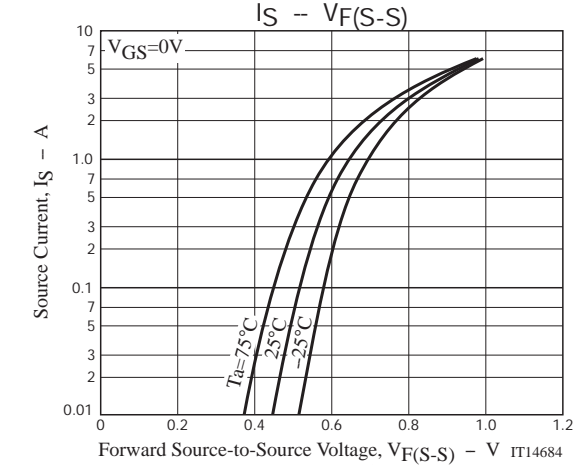
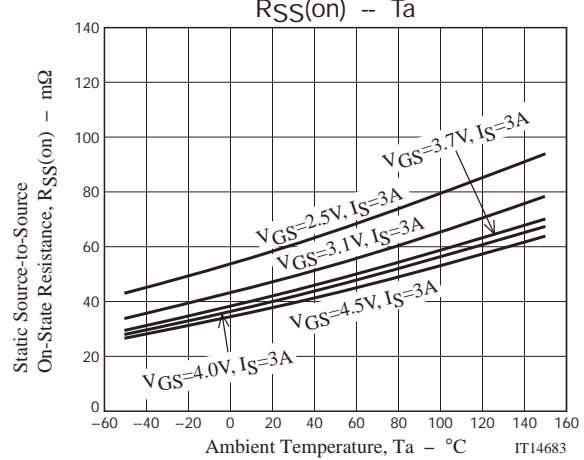
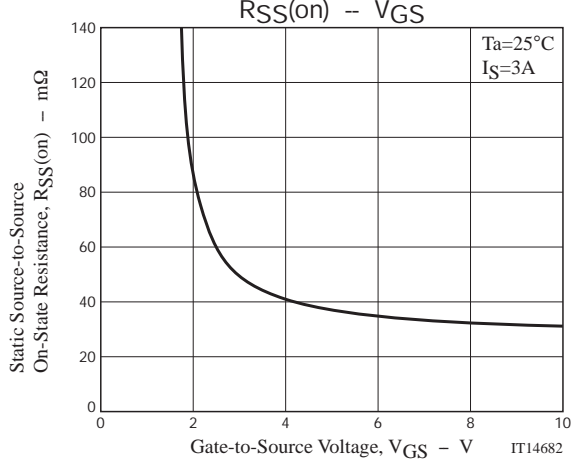
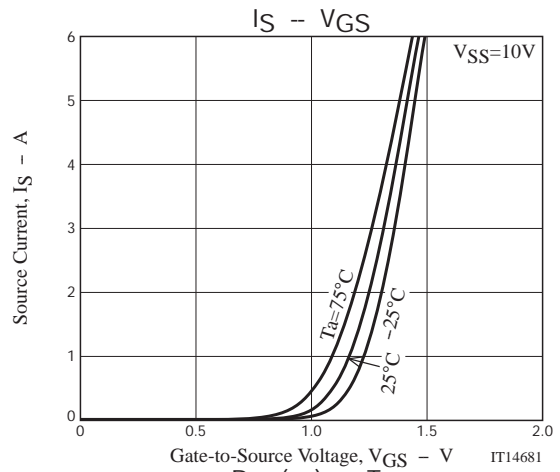
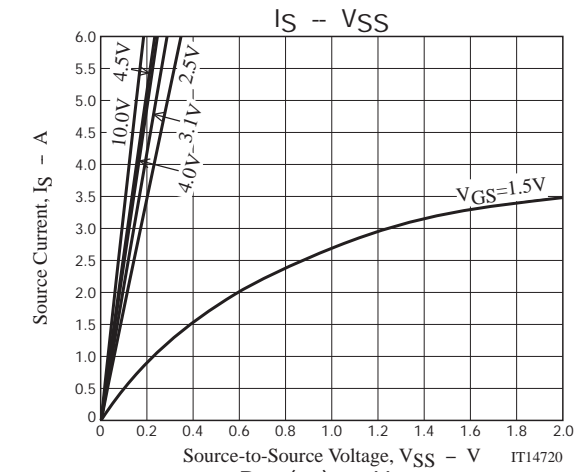
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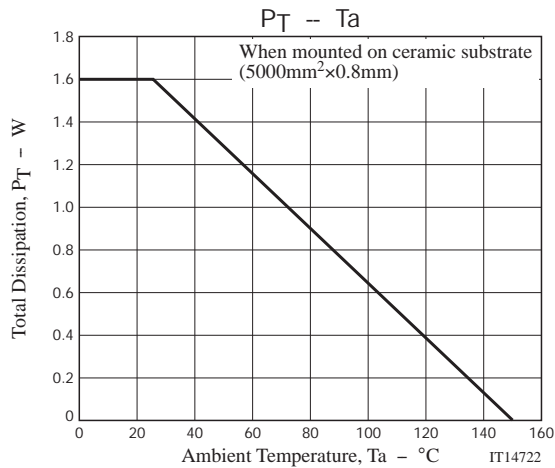
Test Circuit 7

$t_{d(on)}$, t_r , $t_{d(off)}$, t_f



* Note: Connect the measurement terminal reversely if you want to measure the FET2 side.





Note on usage : Since the EFC4612R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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